

# 2MBI300UC-120



## IGBT Module U-Series 1200V / 300A 2 in one-package

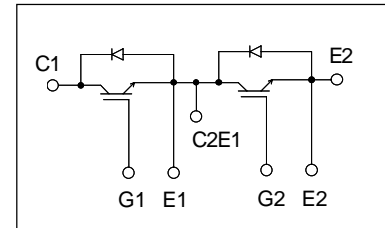
### ■ Features

- High speed switching
- Voltage drive
- Low inductance module structure

### ■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply
- Industrial machines, such as Welding machines

### ■ Equivalent Circuit Schematic



### ■ Maximum ratings and characteristics

#### ● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item	Symbol	Conditions	Rating	Unit	
Collector-Emitter voltage	V <sub>CES</sub>		1200	V	
Gate-Emitter voltage	V <sub>GES</sub>		±20	V	
Collector current	I <sub>c</sub>	Continuous	T <sub>c</sub> =25°C	400	A
			T <sub>c</sub> =80°C	300	
	I <sub>cp</sub>	1ms	T <sub>c</sub> =25°C	800	
			T <sub>c</sub> =80°C	600	
				600	
-I <sub>c</sub>			300		
-I <sub>c</sub> pulse			600		
Collector Power Dissipation	P <sub>c</sub>	1 device	1470	W	
Junction temperature	T <sub>j</sub>		+150	°C	
Storage temperature	T <sub>stg</sub>		-40 to +125		
Isolation voltage	V <sub>iso</sub>	AC:1min.	2500	VAC	
Screw Torque	Mounting *2		3.5	N·m	
	Terminals *2		4.5		

\*1 : All terminals should be connected together when isolation test will be done.

\*2 : Recommendable value : Mounting 2.5 to 3.5 N·m(M5 or M6), Terminals 3.5 to 4.5N·m(M6)

#### ● Electrical characteristics (at T<sub>j</sub>=25°C unless otherwise specified)

Item	Symbols	Conditions	Characteristics			Unit	
			Min.	Typ.	Max.		
Zero gate voltage collector current	I <sub>CES</sub>	V <sub>GE</sub> =0V, V <sub>CE</sub> =1200V	–	–	2.0	mA	
Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V	–	–	400	nA	
Gate-Emitter threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> =20V, I <sub>c</sub> =300mA	4.5	6.5	8.5	V	
Collector-Emitter saturation voltage	V <sub>CE(sat)</sub> (terminal)	V <sub>GE</sub> =15V, I <sub>c</sub> =300A	T <sub>j</sub> =25°C	–	1.90	2.25	V
			T <sub>j</sub> =125°C	–	2.15	–	
	V <sub>CE(sat)</sub> (chip)		T <sub>j</sub> =25°C	–	1.75	2.10	
			T <sub>j</sub> =125°C	–	2.00	–	
Input capacitance	C <sub>ies</sub>	V <sub>CE</sub> =10V, V <sub>GE</sub> =0V, f=1MHz	–	34	–	nF	
Turn-on time	t <sub>on</sub>	V <sub>CC</sub> =600V	–	0.36	1.20	μs	
	t <sub>r</sub>	I <sub>c</sub> =300A	–	0.21	0.60		
	t <sub>r(i)</sub>	V <sub>GE</sub> =±15V	–	0.03	–		
Turn-off time	t <sub>off</sub>	R <sub>G</sub> =1.1 Ω	–	0.37	1.00	μs	
	t <sub>f</sub>		–	0.07	0.30		
Forward on voltage	V <sub>F</sub> (terminal)	V <sub>GE</sub> =0V I <sub>F</sub> =300A	T <sub>j</sub> =25°C	–	1.75	2.05	V
			T <sub>j</sub> =125°C	–	1.85	–	
	V <sub>F</sub> (chip)		T <sub>j</sub> =25°C	–	1.60	1.90	
			T <sub>j</sub> =125°C	–	1.70	–	
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =300A	–	–	0.35	μs	
Lead resistance, terminal-chip*3	R <sub>lead</sub>		–	0.53	–	mΩ	

\*3:Biggest internal terminal resistance among arm.

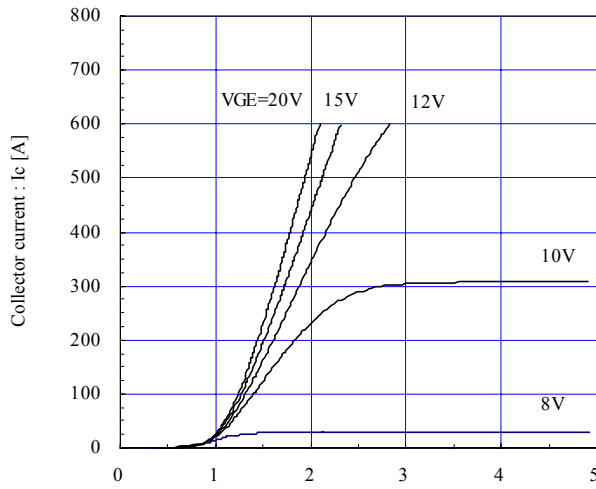
#### ● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance	R <sub>th(j-c)</sub>	IGBT	–	–	0.085	°C/W
	R <sub>th(j-c)</sub>	FWD	–	–	0.14	°C/W
Contact Thermal resistance	R <sub>th(c-f)</sub> *4	With thermal compound	–	0.025	–	°C/W

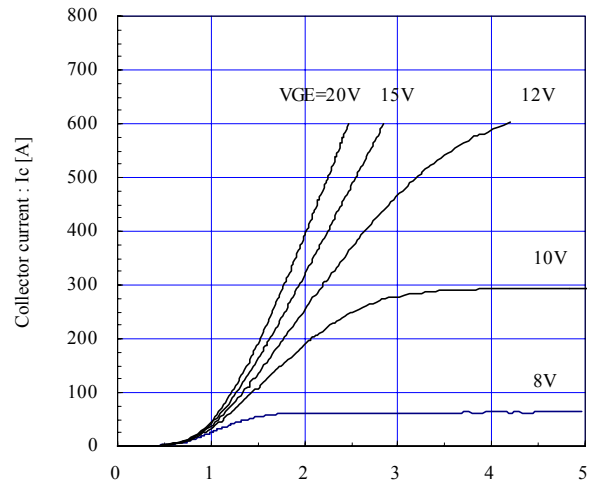
\*4 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

Characteristics (Representative)

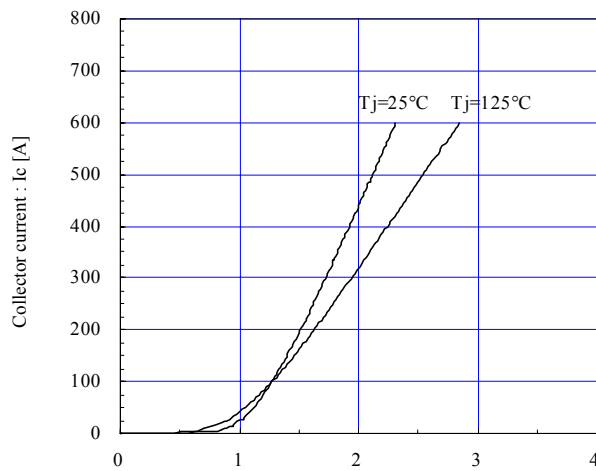
Collector current vs. Collector-Emmitter voltage (typ.)  
Tj= 25°C / chip



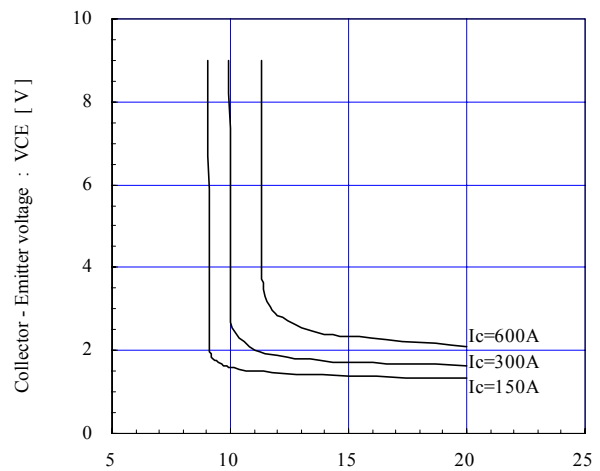
Collector current vs. Collector-Emmitter voltage (typ.)  
Tj= 125°C / chip



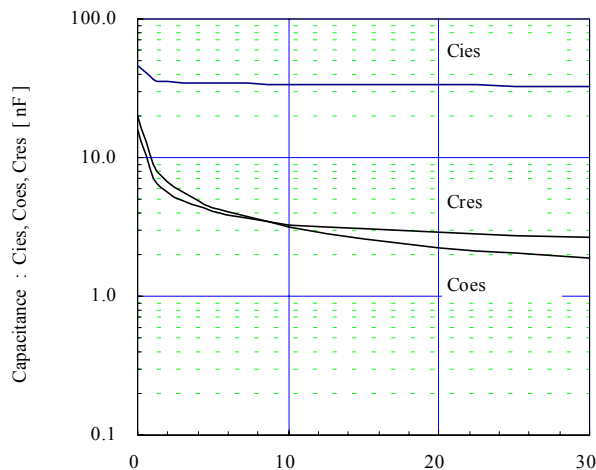
Collector current vs. Collector-Emmitter voltage (typ.)  
VGE=15V / chip



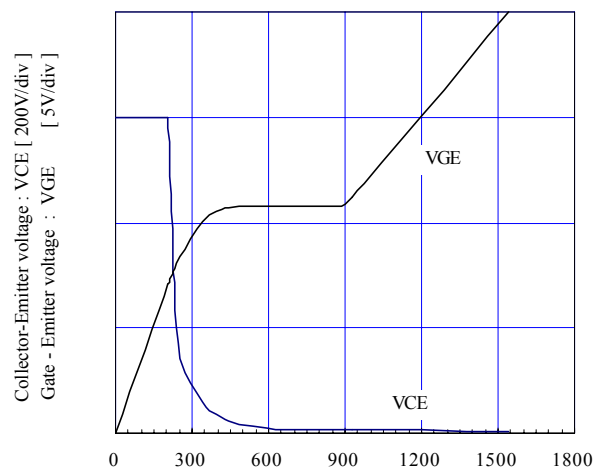
Collector-Emmitter voltage vs. Gate-Emmitter voltage (typ.)  
Tj=25°C / chip

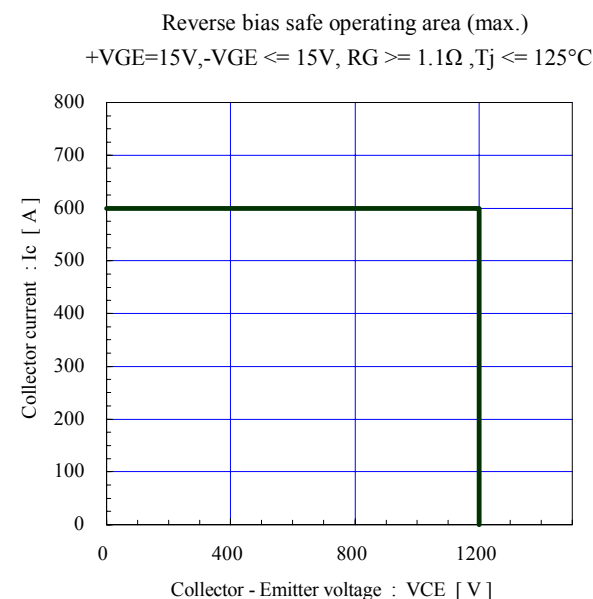
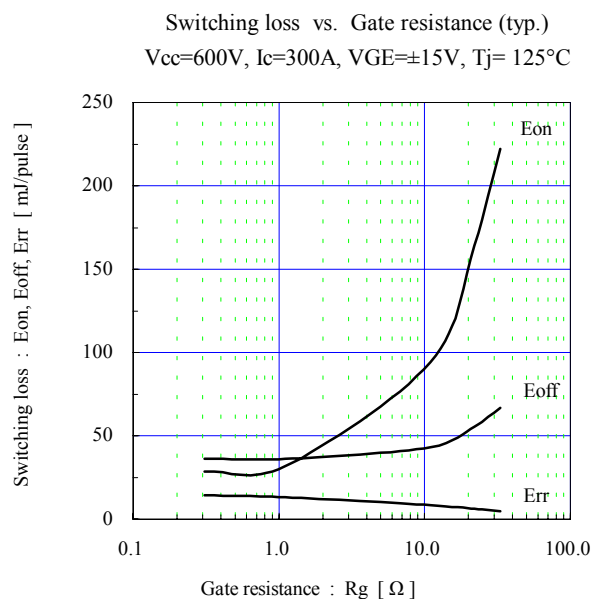
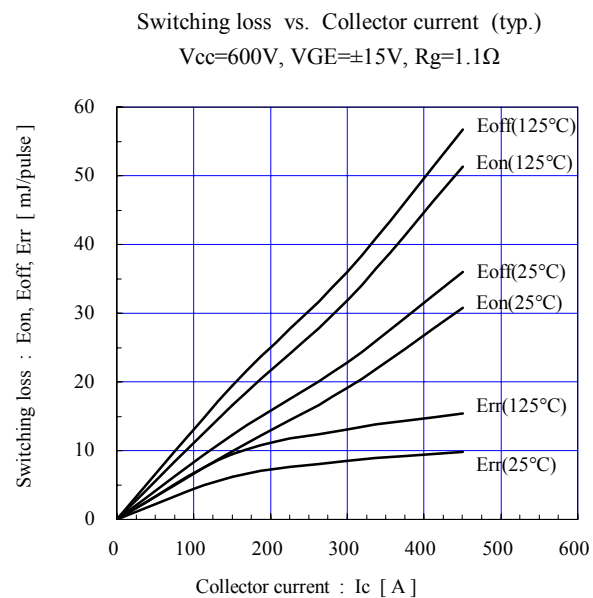
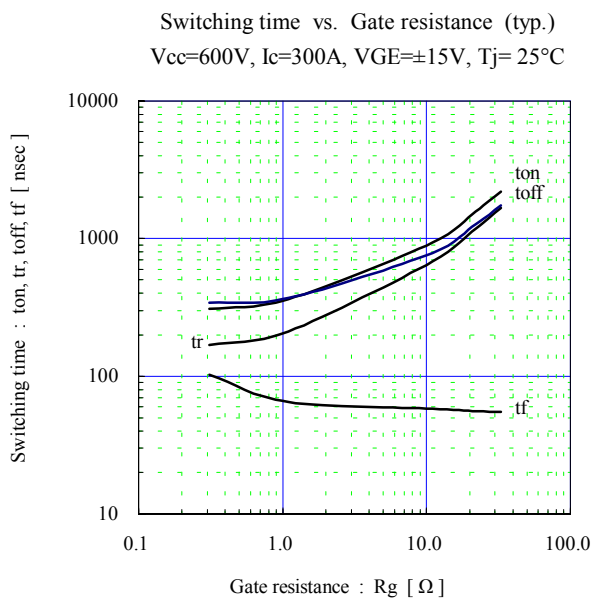
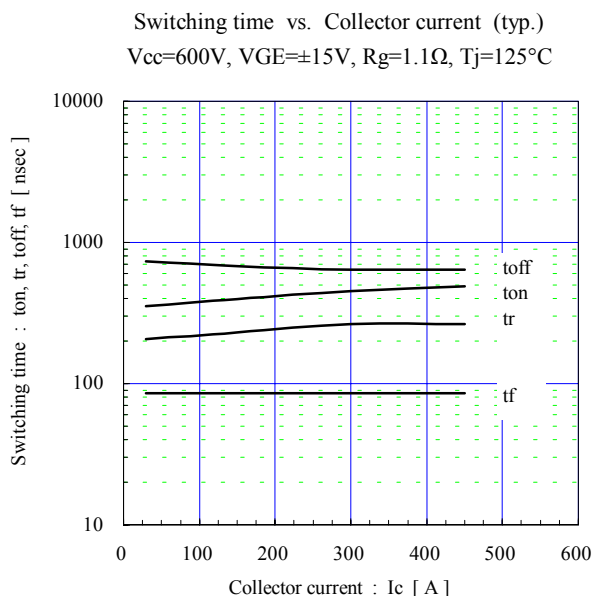
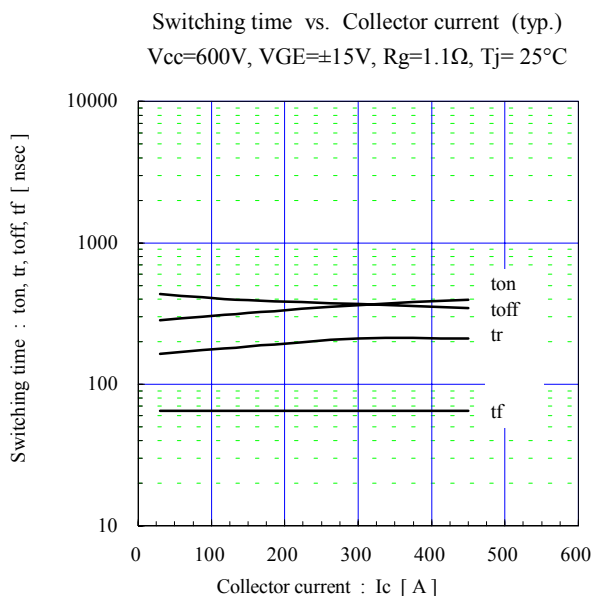


Capacitance vs. Collector-Emmitter voltage (typ.)  
VGE=0V, f= 1MHz, Tj= 25°C

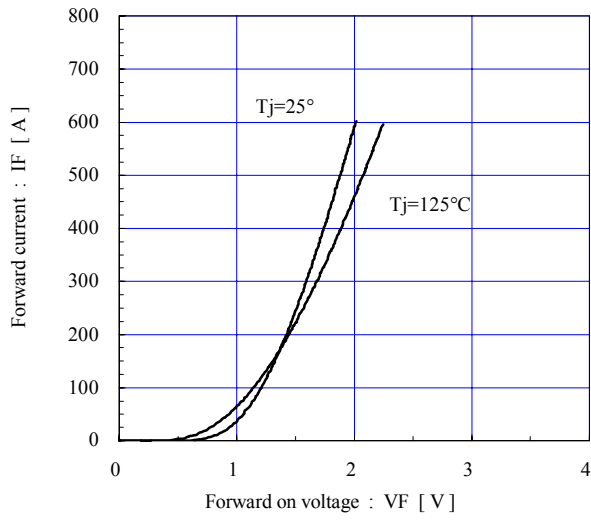


Dynamic Gate charge (typ.)  
Vce=600, Ic=300A, Tj= 25°C

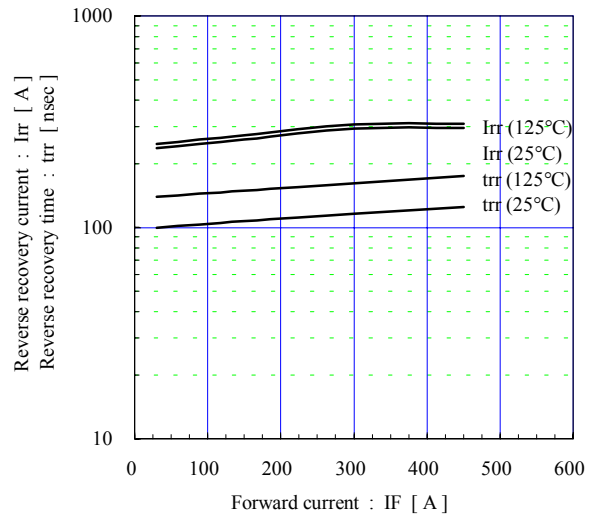




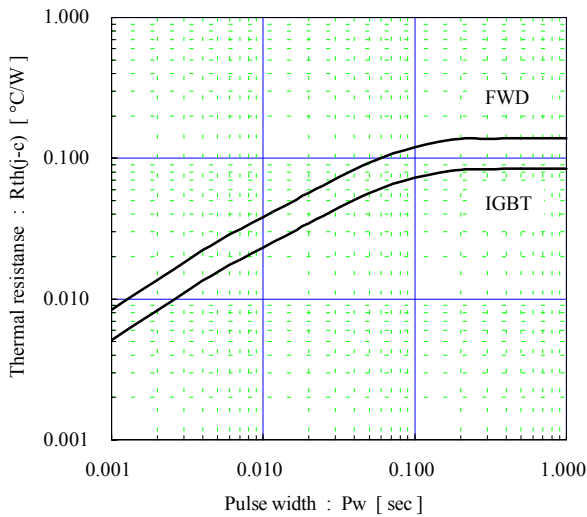
Forward current vs. Forward on voltage (typ.)  
chip



Reverse recovery characteristics (typ.)  
Vcc=600V, VGE=±15V, Rg=1.1Ω



Transient thermal resistance (max.)



■ Outline Drawings, mm

M234

